

Application No.: 09/863,647

Docket No.: JCLA6353

#6

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

LIN ET AL.

Serial No.: 09/863,647

Filed: 05/23/2001

For: A DUAL DAMASCENE PARTIAL GAP FILL)
POLYMER GABRICATION PROCESS)

Examiner: NOVACEK, CHRISTY L.

Art Unit: 2822

Docket No.: JCLA6353

FAX RECEIVED

MAR 28 2003

PETITIONS OFFICE

AMENDMENTS AND RESPONSE TO OFFICE ACTIONAssistant Commissioner of Patents and Trademarks
Washington, DC 20231

Sir:

The Office Action mailed April 08, 2002 has been carefully considered. In response thereto, please enter the following amendments and consider the following remarks.

AMENDMENTS**In The Claims**

Please amend claims 1-5 and 7-10 as follows:

1. A dual damascene partial gap fill polymer fabrication process, comprising:
providing a substrate having a conductive layer therein;
forming a dielectric layer over the substrate and conductive layer;
forming at least one via hole in the dielectric layer, to expose a portion of the conductive layer;
covering the dielectric layer with a gap fill polymer, to fill the via hole;
performing a chemical mechanical polishing step to remove the gap fill polymer layer on the outside of the via hole;